

5DS10B

Switching Diode



Features

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- High – speed

Item	Characteristics
Wafer size	5inch
Chip size	235*235um
Chip Thickness	95 ± 20um
Bump Height	30 ± 15um
Top Metalization	Ti-Ag+Ag Bump
Back Metalization	Ti-Ni-Ag
Dicing	Half Cut

Maximum Ratings @25degC

Item	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V _{RSM}	100	V
Repetitive Peak Reverse Voltage	V _{RRM}	75	V
Repetitive Peak Forward Current	I _{FRM}	500	mA
Continuous Forward Current	I _O	150	mA
Non-Repetitive Peak Forward Current @t=1us	I _{FSM}	2	A
Power Dissipation	P _D	500	mW
Junction Temperature	T _j	175	degC
Storage Temperature	T _{stg}	-65to+175	degC

Electrical Characteristics @25degC

Item	Symbol	Min	Max	Unit	Test Condition
Forward Voltage	V _F		1	V	I _F =10mA
Reverse Current	I _R		25	nA	V _R =20V
Reverse Current	I _R		5	uA	V _R =75V
Junction Capacitance	C _T		4	pF	V _R =0V, f=1MHz
Reverse Recovery Time	t _{rr}		4	nsec	I _F =10mA, V _R =6V, RL=100Ω, irr=1mA

Probing Spec @25degC

Symbol	Min	Max	Unit	Test Condition
V _{F1}		850	mV	I _F =10mA
V _{F2}		1	V	I _F =100mA
V _{F3}		1.3	V	I _F =200mA
I _{R1}		25	nA	V _R =30V
I _{R2}		100	nA	V _R =75V
I _{R2}		200	nA	V _R =100V
B _V	135		V	I _R =50uA
C _T		4	pF	V _R =0V, f=1MHz
t _{rr}		4	nsec	I _F =10mA, V _R =6V, RL=100Ω, irr=1mA

Note Equivalent type : 1N4148

SheetNo.

Rev.